

**isc Silicon NPN Power Transistor**

**ET190**

**DESCRIPTION**

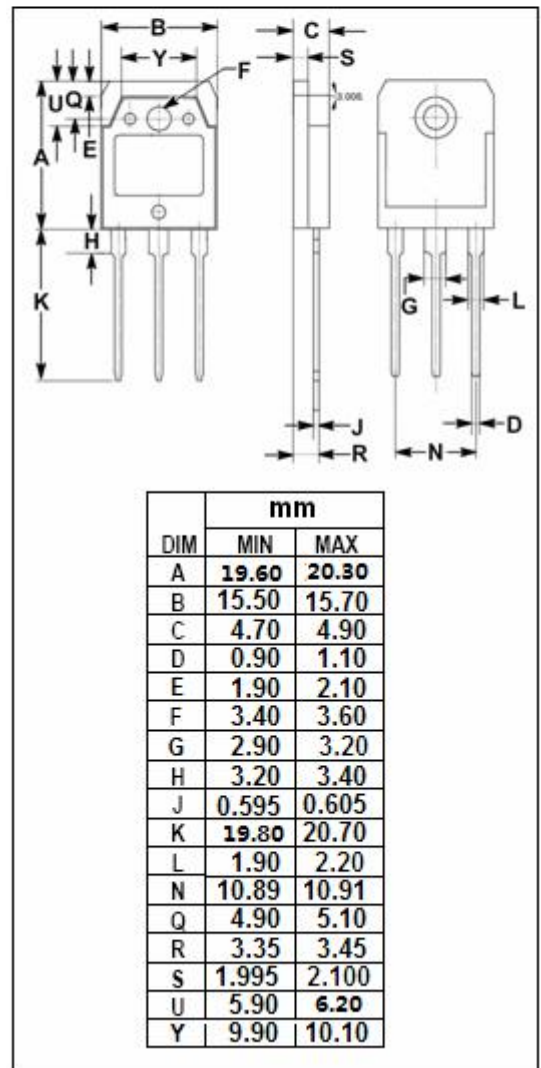
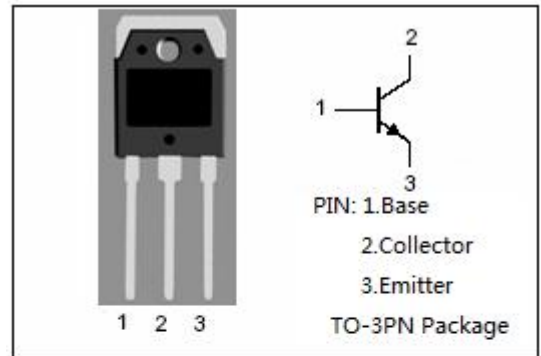
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = 2.0V(\text{Min}) @ I_C = 8A$
- High reliability
- High D.C current gain

**APPLICATIONS**

- Power amplifier applications

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	600	V
$V_{CEO}$	Collector-Emitter Voltage	600	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	8	A
$I_B$	Base Current-Continuous	1	A
$P_C$	Collector Power Dissipation	80	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc Silicon NPN Power Transistor****ET190****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}; I_B=0$	600			V
$V_{(BR)CBO}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}; I_B=0$	600			V
$V_{CBO(SUS)}$	Collector-Emitter Breakdown Voltage	$I_C=100\text{mA}; I_B=0$	450			V
$V_{EBO}$	Emitter-Base Breakdown Voltage	$I_{EBO}=200\text{mA}$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.1\text{A}$			1.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=5\text{A}; I_B=0.1\text{A}$			1.8	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=600\text{V}; I_E=0$			1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			200	mA
$h_{FE-1}$	DC Current Gain	$I_C=5\text{A}; V_{CE}=5\text{V}$	200			